Atty. Dkt. No. 039153-0450 (G1155)

Amendments to the Specification:

Please amend the specification as follows:

Please replace paragraph numbers [0001], [0014], [0035] and [0036] with the following rewritten paragraphs:

[0001]   This application is related to U.S. Patent Application No. 10/016,439, Attorney Docket No. 39153/447 (G1152), entitled METHOD OF EXTENDING THE AREAS OF CLEAR FIELD PHASE SHIFT GENERATION; U.S. Patent Application No. 10/016,710, Attorney Docket No. 39153/448 (G1153), entitled METHOD OF ENHANCING CLEAR FIELD PHASE SHIFT MASKS WITH CHROME BORDER AROUND PHASE 180 REGIONS; U.S. Patent Application No. 10/016,702, Attorney Docket No. 39153/449 (G1154), entitled METHOD OF ENHANCING CLEAR FIELD PHASE SHIFT MASKS BY ADDING PARALLEL LINE TO PHASE 0 REGION; and U.S. Patent Application No. 10/016,441, Attorney Docket No. 39153/451 (G1156), entitled METHOD OF ENHANCING CLEAR FIELD PHASE SHIFT MASKS WITH BORDER AROUND OUTSIDE EDGES OF PHASE ZERO REGIONS, all of which are assigned to the same assignee as the present application.

[0014]   An enhanced phase shift approach was developed to reduce the transition regions and move those regions away from the active edge to wider poly or corners of poly patterns where linewidth loss would have little or no impact. Examples of this enhanced phase shifting approach are described in U.S. Patent Application Serial No. 09/772,577 entitled PHASE SHIFT MASK AND SYSTEM AND METHOD FOR MAKING THE SAME, filed on January 30, 2001, by Todd P. Lukanc (one of the inventors of the present application) and assigned to the assignee of the present application, incorporated herein by reference, now U.S. Patent No. 6,534,224.

[0035]   FIGURE 2 illustrates a plan view of a phase mask 200 formed or designed utilizing the process described with reference to FIGURE 1. Phase mask 200 includes poly

-2-

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PAGE 3/13 * RCVD AT 1/22/2004 1:23:46 PM [Eastern Standard Time] * SVR:USPTO-EFXRF-1/2 * DNIS:8729306 * CSID: * DURATION (mm-ss):06-18

regions 210, phase 180 regions 220, phase 0 regions 230, and phase 180 boundary regions 240. Poly regions 210 (depicted in FIGURE 2 as cross-hatched areas) are critical poly sections. Phase 180 regions 220 and phase 0 regions 230 help to define poly regions 210 and can be created by hand or using a computer software program configured for the designing of phase masks. Phase 180 boundary regions 240 can be formed outside edges of defined phase 180 regions 220 that are not defining the poly pattern.

[0036]   Phase mask 200 also can include a region 250 outside of defined areas. In an exemplary embodiment, region 250 (depicted in FIGURE 2 without hashing) is assigned a phase of zero.

-3-